RENESAS TECHNICAL UPDATE

TOYOSU FORESIA, 3-2-24, Toyosu, Koto-ku, Tokyo 135-0061, Japan
Renesas Electronics Corporation

Product Category	MPU/MCU		Document No.	TN-RA*-A0050A/E	Rev.	1.00
Title	RA4M1 Group, RA4W1 Group, RA6M1 Group, RA6M2 Group, RA6M3 Group, correction of Battery Backup Function		Information Category	Technical Notification		
Applicable Product	RA4M1 Group RA4W1 Group RA6M1 Group RA6M2 Group RA6M3 Group	Lot No.	Reference Document	RA4M1 Group User's Manual Hardware Rev.1.00 RA4W1 Group User's Manual Hardware Rev.1.00 RA6M1 Group User's Manual Hardware Rev.1.00 RA6M2 Group User's Manual Hardware Rev.1.10 RA6M3 Group User's Manual Hardware Rev.1.10		
		All				

The description of Backup Registers is corrected.

RA4M1, RA4W1

[Before]

12. Battery Backup Function

12.1 Overview

12.1.5 Backup Registers

The battery-powered area provides 512 one-byte backup registers. These registers retain data only when VBATT is supplied and VCC is powered off. This memory is checked by the VBATT pin low voltage detection.

[After]

12. Battery Backup Function

12.1 Overview

12.1.5 Backup Registers

The battery-powered area provides 512 one-byte backup registers. These registers retain data when the battery-powered area is powered from VCC pin or VBATT pin. This memory is checked by the VBATT pin low voltage detection.

RA6M1, RA6M2, RA6M3

[Before]

12. Battery Backup Function

12.1 Overview

12.1.3 Backup Registers

The battery-powered area provides 512 one-byte backup registers. These registers retain data only when VBATT is supplied and VCC is powered off.

[After]

12. Battery Backup Function

12.1 Overview

12.1.3 Backup Registers

The battery-powered area provides 512 one-byte backup registers. These registers retain data when the battery-powered area is powered from VCC pin or VBATT pin.